

Dual P-CHANNEL ENHANCEMENT MODE MOSFET
Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	I_D max
-20V	260m Ω @ $V_{GS} = -4.5V$	-0.9 A
	500m Ω @ $V_{GS} = -2.5V$	
	1000m Ω @ $V_{GS} = -1.8V$	

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Battery Disconnect Switch
- Load Switch for Power Management Functions

Features

- Low $R_{DS(on)}$ – Minimizes Conduction Losses
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (Approximate)

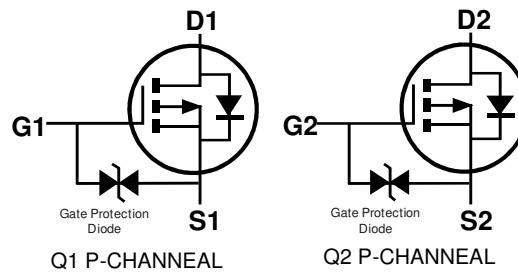


ESD PROTECTED

SOT363

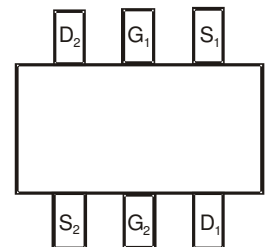


Top View



Q1 P-CHANNEL

Q2 P-CHANNEL


 Top View
Pin out

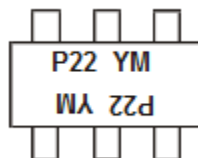
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2200UDW-7	SOT363	3,000/Tape & Reel
DMP2200UDW-13	SOT363	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com>.

Marking Information

SOT363



P22 = Marking Code
 YM = Date Code Marking
 Y or Y= Year (ex: B = 2014)
 M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020
Code	B	C	D	E	F	G	H

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±8	V
Continuous Drain Current (Note 6)	I _D	T _A = +25°C	-0.9
		T _A = +85°C	-0.7

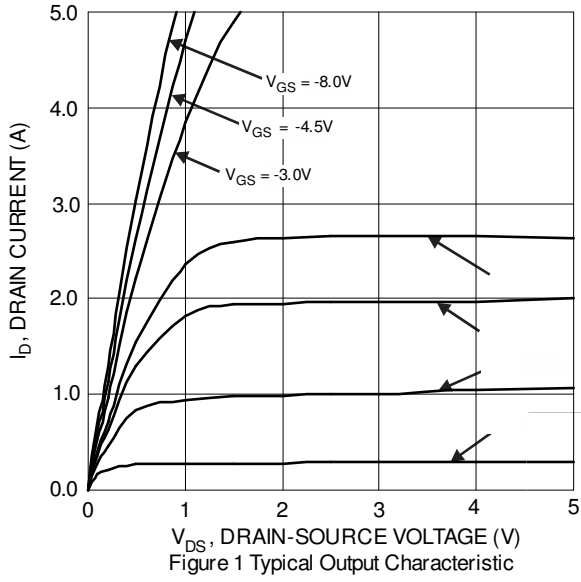
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	0.45	W
Total Power Dissipation (Note 6)		0.6	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	275	°C/W
Thermal Resistance, Junction to Ambient (Note 6)		208	
Thermal Resistance, Junction to Case	R _{θJC}	72	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -16V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.4	—	-1.2	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	180	260	mΩ	V _{GS} = -4.5V, I _D = -0.88A
			240	500		V _{GS} = -2.5V, I _D = -0.71A
			320	1,000		V _{GS} = -1.8V, I _D = -0.20A
Diode Forward Voltage	V _{SD}	—	-0.8	-1.2	V	V _{GS} = 0V, I _S = -0.48A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	184	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{OSS}	—	26.4	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	18.5	—	pF	
Gate Resistance	R _g	—	221	—	Ω	V _{DS} = V _{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	—	2.1	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -1.7A
Gate-Source Charge	Q _{gs}	—	0.4	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.5	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	9.8	—	ns	V _{DD} = -10V, I _D = -1.5A, V _{GS} = -4.5V, R _{GEN} = 1Ω
Turn-Off Delay Time	t _{D(OFF)}	—	24.4	—	ns	
Turn-On Rise Time	t _r	—	88	—	ns	
Turn-Off Fall Time	t _f	—	45	—	ns	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.



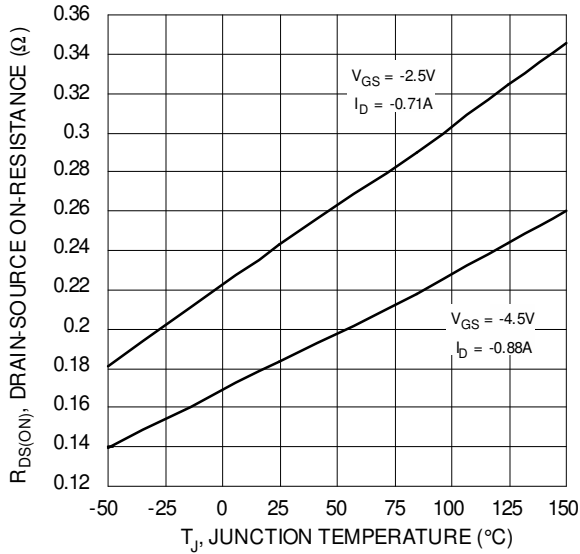


Figure 7 On-Resistance Variation with Temperature

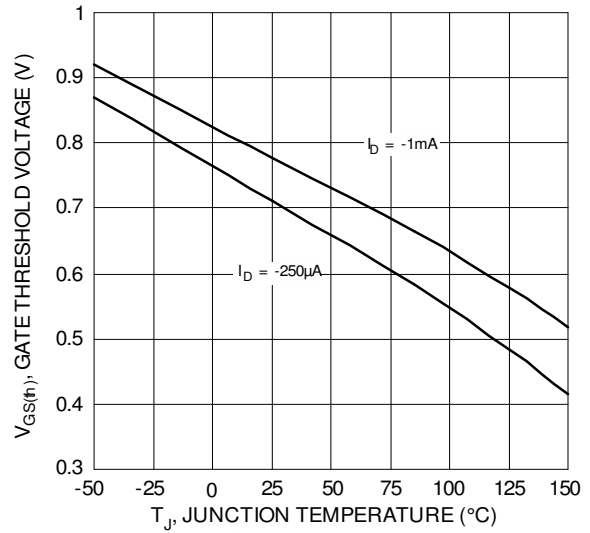


Figure 8 Gate Threshold Variation vs. Junction Temperature

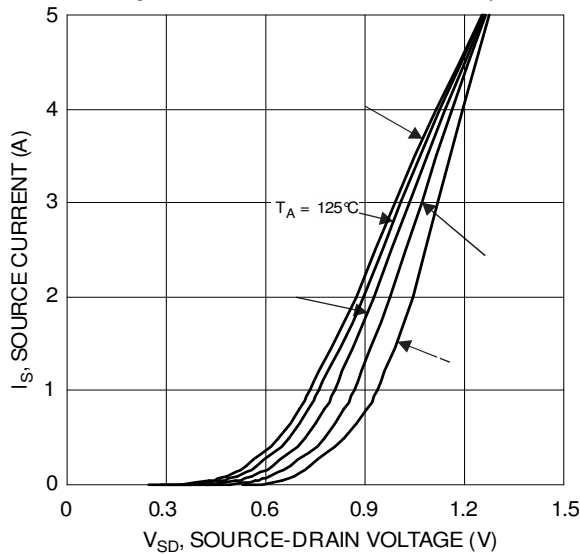


Figure 9 Diode Forward Voltage vs. Current

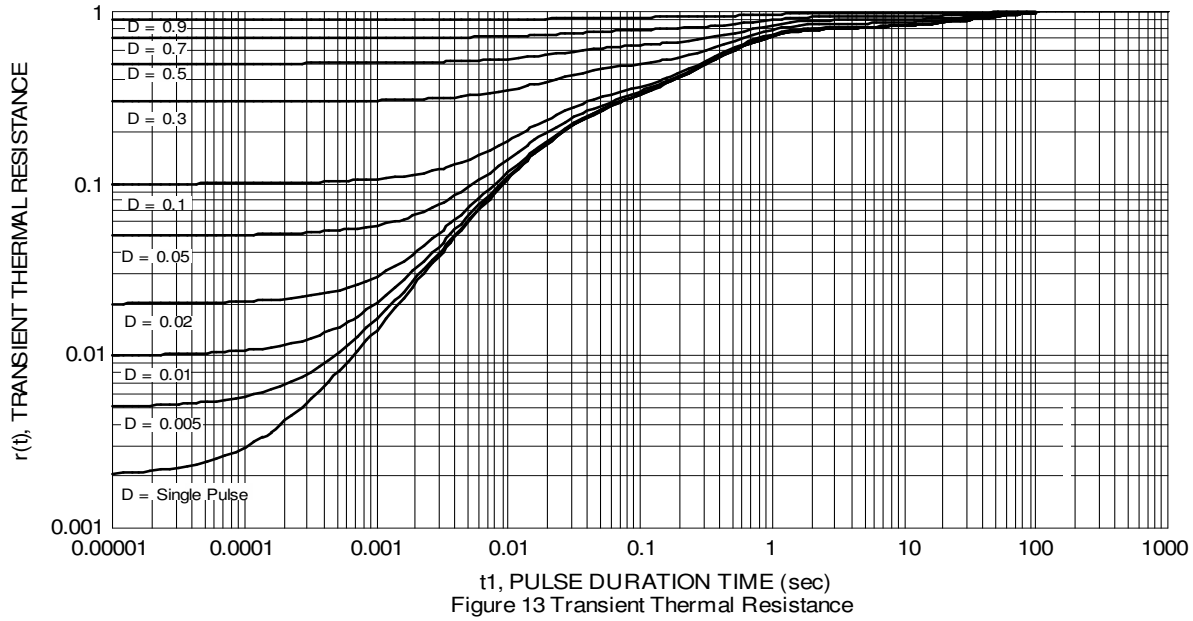


Figure 13 Transient Thermal Resistance

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND,